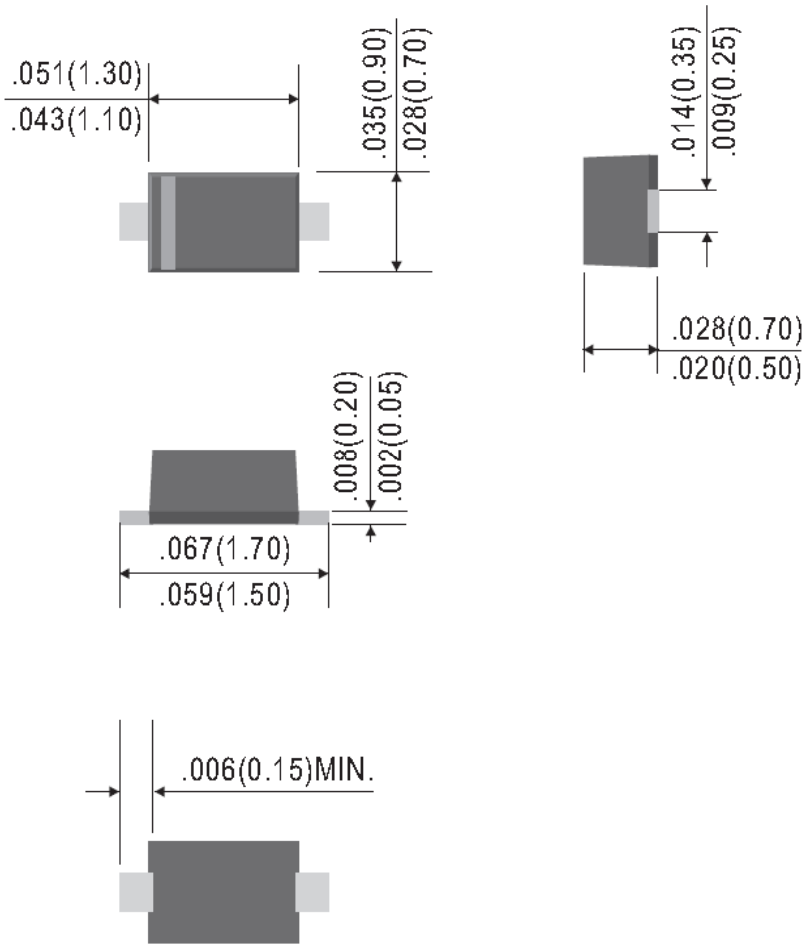
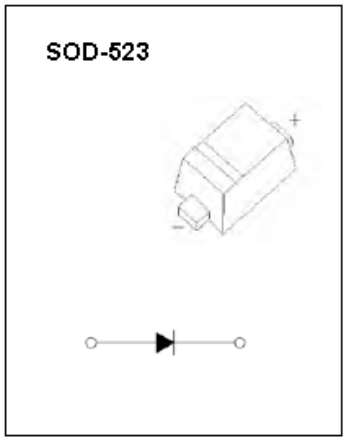
BAS16X

Plastic-Encapsulate Diodes





Dimensions in inches and (millimeters)

FEATURES

·High-Speed Switching Applications
·Lead Finish: 100% Matte Sn (Tin)
·Qualified Reflow Temperature: 260 ℃
·Pb-Free package is available
·RoHS product for packing code suffix "G"
·Halogen free product for packing code suffix "H"
·Moisture Sensitivity Level 1
·Polarity: Color band denotes cathode end

MARKING: **A6**

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Maximum Ratings (T_a=25°C unless otherwise noted)			
Parameter	**Symbol**	**Limit**	**Unit**
DC Reverse Voltage	V_R	75	V
Forward Current	I_F	200	mA
Peak Forward Surge Current	I_{FSM}	500	mA
Power Dissipation	P_D	150	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	833	°C/W
Junction temperature	T_J	150	°C
Operating/ Storage temperature	T_{STG}	-55~+150	°C

Electrical Characteristics (T_a=25°C unless otherwise noted)						
Parameter	**Symbol**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Reverse Voltage	$V_{(BR)}$	I_R= 100μA	75	—	—	V
Forward Voltage	V_{F1}	I_F=1mA	—	—	0.715	V
	V_{F2}	I_F=10mA	—	—	0.855	
	V_{F3}	I_F=50mA	—	—	1.00	
	V_{F4}	I_F=150mA	—	—	1.25	
Reverse Current	I_R	V_R=75V	—	—	1	μA
Reverse Recovery Time	t_{rr}	I_F=I_R=10mAdc I_{rr}=0.1XI_R, R_L=50Ω	—	—	6	ns
Forward Recovery Voltage	V_{FR}	I_F=10mA, t_r= 20ns	—	—	1.75	V
Diode Capacitance	C_D	V_R=0V, f=1MHz	—	—	2	pF
Stored Charge	Q_S	I_F=10mA, V_R=5.0V ,R_L=500Ω	—	—	45	pC

Typical Characteristics